

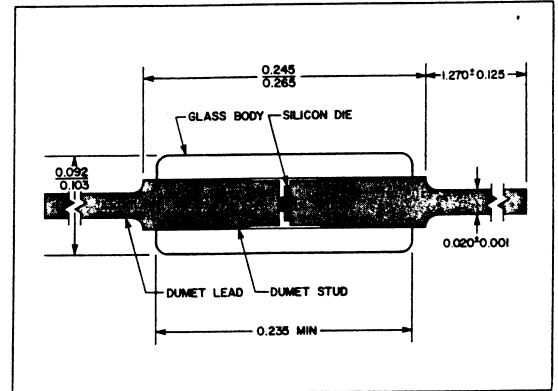
PRODUCT SPECIFICATIONS

HIGH CONDUCTANCE, GENERAL PURPOSE

SILICON PLANODE**

1N461A 1N463A
 1N462A 1N464A

The 1N461A PLANODE** family, with one-piece whiskerless planar construction, offers the ultimate in electrical and mechanical reliability. Die and studs are metallurgically bonded into one massive structure. Thermal and mechanical shock are distributed throughout this structure instead of concentrating at a delicate whisker contact. PLANODE** construction, plus Raytheon's MARK X and optional X-L Reliability Processing, insures ultimate reliability.



MECHANICAL DATA

CASE:

JEDEC DO-7

MARKING:

Standard E.I.A. color code bands starting at cathode end.

ELECTRICAL DATA

ABSOLUTE MAXIMUM RATINGS:

Average Rectified Current, I_O , 25° C	200 mA
Average Rectified Current, I_O , 150° C	70 mA
Surge Current (1 sec), i_f (surge), 25° C	1500 mA
Surge Current (1 sec), i_f (surge) 150° C	1000 mA
Power Dissipation @ 25° C	500 mW
Operating Temperature	-65° C to +200° C
Storage Temperature	-65° C to +200° C

ELECTRICAL CHARACTERISTICS: @ 25° C (unless otherwise noted)

Type	Working Inverse Voltage (Volts)	Minimum Forward Current @ 1.0 Volt (mA)	Maximum Inverse Current at Specified Voltage (μA)	25° C	150° C	Volts	Minimum Saturation Voltage @ 100 μA (Volts)
1N461A	25	100	0.5	30	25	30	
1N462A	60	100	0.5	30	60	70	
1N463A	175	100	0.5	30	175	200	
1N464A	125	100	0.5	30	125	150	

